

L Number	Hits	Search Text	DB	Time stamp
1	360	438/471	USPAT	2004/04/14 10:52
2	171	438/474	USPAT	2004/04/14 10:52
3	157	438/475	USPAT	2004/04/14 10:52
4	983	438/680	USPAT	2004/04/14 10:52
5	472	438/681	USPAT	2004/04/14 10:52
6	1448	438/687	USPAT	2004/04/14 10:53
7	160	438/679	USPAT	2004/04/14 10:53
8	1073	438/675	USPAT	2004/04/14 10:53
9	1442	438/706	USPAT	2004/04/14 10:53
10	1235	438/700	USPAT	2004/04/14 10:53
11	404	438/715	USPAT	2004/04/14 10:53
12	143	438/732	USPAT	2004/04/14 10:53
13	213	438/733	USPAT	2004/04/14 10:53
14	489	438/740	USPAT	2004/04/14 10:53
15	318	438/905	USPAT	2004/04/14 10:53
16	570	438/906	USPAT	2004/04/14 10:54
-	0	10/636168	USPAT	2004/04/14 09:15
-	1	("6126806").PN.	USPAT	2004/04/14 09:15
-	1	("6235406").PN.	USPAT	2004/04/14 09:15
-	1	("6355571").PN.	USPAT	2004/04/14 09:16
-	0	(dual adj damascene) and trench and CMP and (annealing adj process) and in-situ and cooling and chamber and hydrogen and cleaning	USPAT	2004/04/14 09:19
-	0	(dual adj damascene) and trench and CMP and in-situ and cooling and chamber and hydrogen and cleaning and heating	USPAT	2004/04/14 10:52
-	3	(dual adj damascene) and trench and CMP and in-situ and cooling and chamber and hydrogen and cleaning	USPAT	2004/04/14 09:21
-	1		USPAT	2004/04/14 09:21
-	1		USPAT	2004/04/14 09:22
-	1		USPAT	2004/04/14 09:22
-	1		USPAT	2004/04/14 09:22
-	1		USPAT	2004/04/14 09:22
-	1		USPAT	2004/04/14 09:23
-	1		USPAT	2004/04/14 09:24
-	1		USPAT	2004/04/14 09:24
-	1		USPAT	2004/04/14 09:24
-	1		USPAT	2004/04/14 09:25
-	1		USPAT	2004/04/14 09:25
-	1		USPAT	2004/04/14 09:25
-	1		USPAT	2004/04/14 09:25
-	1		USPAT	2004/04/14 09:26
-	1		USPAT	2004/04/14 09:26
-	1		USPAT	2004/04/14 09:26
-	1	("5935767").PN.	USPAT	2004/04/14 09:27
-	1	("6380096").PN.	USPAT	2004/04/14 09:27
-	1	(("5935767").PN.) and (dual or damascene or treanch or hole or opening or via or aperture or cleaning or process or CMP or chamber or reactive or reaction or hydrogen or polymer or in-situ or metal or conductive or insulating or dielectric or side or wall or photo or resist or upper or lower or line or substrate or pattern or single or gas or inert or pressure or power or SIOC or copper or seed or material or oxide or remove or removing or burying or implementing or cooling opr cool or annealing or heating or temperature)	USPAT	2004/04/14 09:36
-	1	("5935762").PN.	USPAT	2004/04/14 09:35

-	1	((("5935762").PN.) and (dual or damascene or trench or hole or opening or via or aperture or cleaning or process or CMP or chamber or reactive or reaction or hydrogen or polymer or In-situ or metal or conductive or insulating or dielectric or side or wall or photo or resist or upper or lower or line or substrate or pattern or single or gas or Inert or pressure or power or SiOC or copper or seed or material or oxide or remove or removing or burying or implementing or cooling opr cool or annealing or heating or temperature))	USPAT	2004/04/14 09:42
-	1	((("6380096").PN.) and (dual or damascene or trench or hole or opening or via or aperture or cleaning or process or CMP or chamber or reactive or reaction or hydrogen or polymer or In-situ or metal or conductive or insulating or dielectric or side or wall or photo or resist or upper or lower or line or substrate or pattern or single or gas or Inert or pressure or power or SiOC or copper or seed or material or oxide or remove or removing or burying or implementing or cooling opr cool or annealing or heating or temperature))	USPAT	2004/04/14 09:48
-	1	((("6126806").PN.) and (dual or damascene or trench or hole or opening or via or aperture or cleaning or process or CMP or chamber or reactive or reaction or hydrogen or polymer or In-situ or metal or conductive or insulating or dielectric or side or wall or photo or resist or upper or lower or line or substrate or pattern or single or gas or Inert or pressure or power or SiOC or copper or seed or material or oxide or remove or removing or burying or implementing or cooling opr cool or annealing or heating or temperature))	USPAT	2004/04/14 09:49
-	1	((("6235406").PN.) and (dual or damascene or trench or hole or opening or via or aperture or cleaning or process or CMP or chamber or reactive or reaction or hydrogen or polymer or In-situ or metal or conductive or insulating or dielectric or side or wall or photo or resist or upper or lower or line or substrate or pattern or single or gas or Inert or pressure or power or SiOC or copper or seed or material or oxide or remove or removing or burying or implementing or cooling opr cool or annealing or heating or temperature))	USPAT	2004/04/14 09:49
-	1	((("6355571").PN.) and (dual or damascene or trench or hole or opening or via or aperture or cleaning or process or CMP or chamber or reactive or reaction or hydrogen or polymer or In-situ or metal or conductive or insulating or dielectric or side or wall or photo or resist or upper or lower or line or substrate or pattern or single or gas or Inert or pressure or power or SiOC or copper or seed or material or oxide or remove or removing or burying or implementing or cooling opr cool or annealing or heating or temperature))	USPAT	2004/04/14 09:51
-	1	((("5529953").PN.) and (dual or damascene or trench or hole or opening or via or aperture or cleaning or process or CMP or chamber or reactive or reaction or hydrogen or polymer or In-situ or metal or conductive or insulating or dielectric or side or wall or photo or resist or upper or lower or line or substrate or pattern or single or gas or Inert or pressure or power or SiOC or copper or seed or material or oxide or remove or removing or burying or implementing or cooling opr cool or annealing or heating or temperature))	USPAT	2004/04/14 09:51
-	1	((("5529953").PN.) and (dual or damascene or trench or hole or opening or via or aperture or cleaning or process or CMP or chamber or reactive or reaction or hydrogen or polymer or In-situ or metal or conductive or insulating or dielectric or side or wall or photo or resist or upper or lower or line or substrate or pattern or single or gas or Inert or pressure or power or SiOC or copper or seed or material or oxide or remove or removing or burying or implementing or cooling opr cool or annealing or heating or temperature))	USPAT	2004/04/14 09:52
-	1	((("5614765").PN.) and (dual or damascene or trench or hole or opening or via or aperture or cleaning or process or CMP or chamber or reactive or reaction or hydrogen or polymer or In-situ or metal or conductive or insulating or dielectric or side or wall or photo or resist or upper or lower or line or substrate or pattern or single or gas or Inert or pressure or power or SiOC or copper or seed or material or oxide or remove or removing or burying or implementing or cooling opr cool or annealing or heating or temperature))	USPAT	2004/04/14 09:52

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4/14/04